

版本	修订日期	有修订的页码	修订涉及的内容	拟制	审核
A	2022.2.12	ALL	参照 AOS-AOD294A 规格书创建本厂规格书	庞隆基	陈逸晞

/ Descriptions

TO-252 N

N-CHANNEL MOSFET in a TO-252 Plastic Package.

/ Features

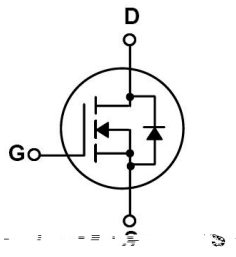
 $R_{DS(on)}$ C_{rss} Low $R_{DS(on)}$, low gate charge, low C_{rss} , fast switching, HF Product.

/ Applications

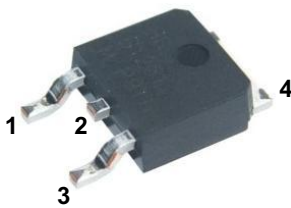
DC/DC

Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products.

/ Equivalent Circuit



/ Pinning



PIN1 G

PIN 2 D

PIN 3 S

PIN 4 D

/ Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

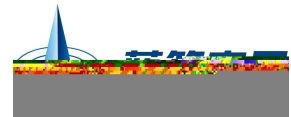
Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	100	V
Drain Current		$I_D(T_c=25)$	55	A
Drain Current - Pulsed		I_{DM}	138	A
Gate-Source Voltage		V_{GS}	± 20	V
Avalanche Current		I_{AS}	7.0	A
Single Pulsed Avalanche Energy(L=0.5mH)		E_{AS}	24.5	mJ
Power Dissipation		$P_D(T_c=25)$	73	W
Storage Temperature Range		T_{stg}	-55 to 150	$^{\circ}C$
Thermal Resistance-Junction to Ambient	$t \leq 10s$	$R_{\theta JA}$	20	/W
	Steady-State		50	
Thermal Resistance-Junction to Case	Steady-State	$R_{\theta JC}$	1.7	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	100	108		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V$ $V_{GS}=0V$			1.0	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	1.5	1.8	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=20A$		13	15	m Ω
		$V_{GS}=4.5V$ $I_D=10A$		18	25	
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=1A$			1.2	V
Gate resistance	R_g	$V_{GS}=0V$ $V_{DS}=0V$, $f=1MHz$		1.5		Ω
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		1140		pF
Output Capacitance	C_{oss}			600		
Reverse Transfer Capacitance	C_{rss}			60		
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10V$, $V_{DS}=50V$, $I_D=20A$		32.5		nC
Total Gate Charge	$Q_{g(4.5V)}$			15.5		
Gate Source Charge	Q_{gs}			6.5		
Gate Drain Charge	Q_{gd}			5		

BRCS150N10SDP

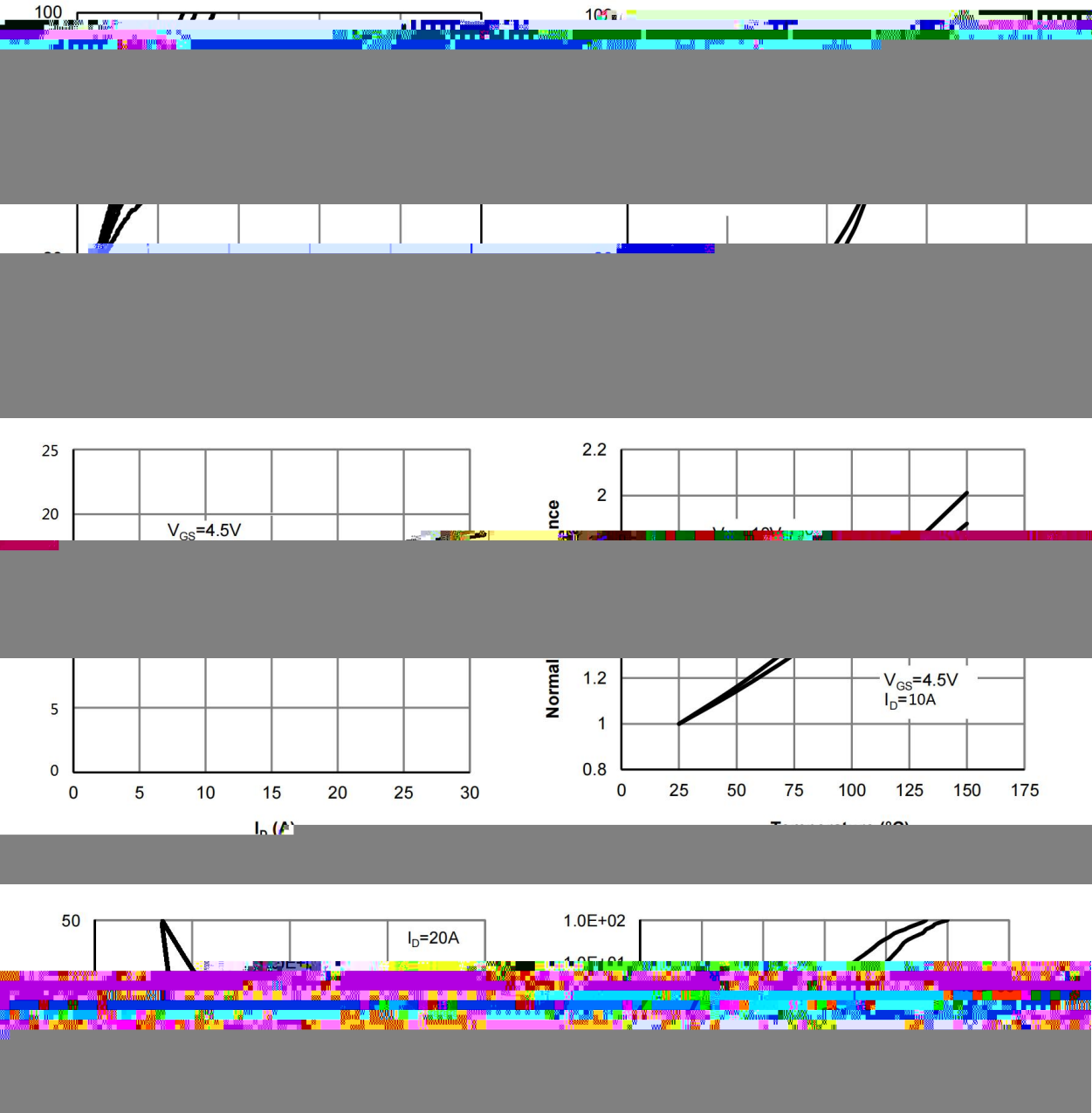
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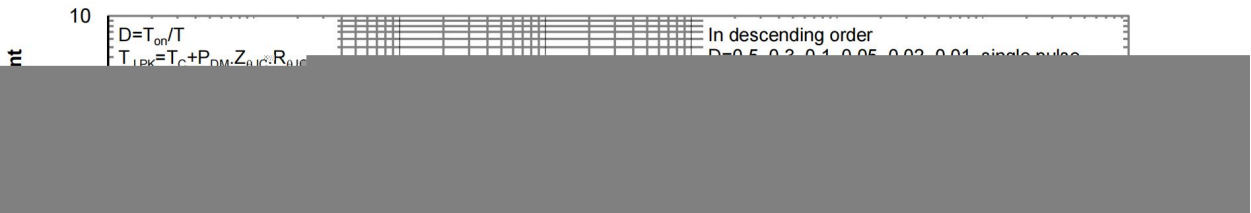
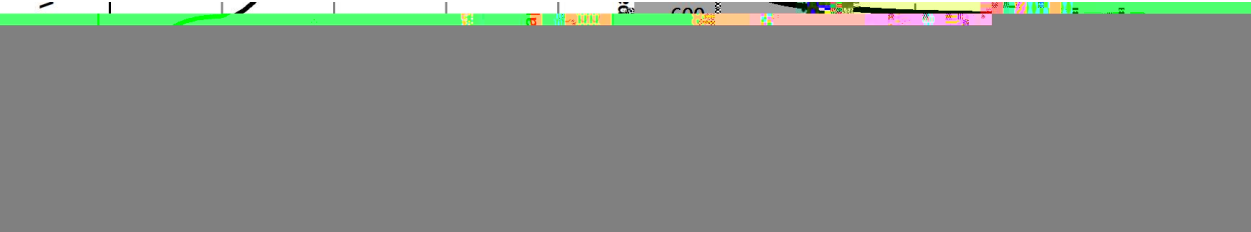
DATA SHEET

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=50V$ $R_L=2.5\Omega$ $R_{GEN}=3\Omega$		7		ns
Turn-On Rise Time	t_r			3		
Turn-Off Delay Time	$t_{d(off)}$			27		
Turn-Off Fall Time	t_f			4		

/ Electrical Characteristic Curve



/ Electrical Characteristic Curve

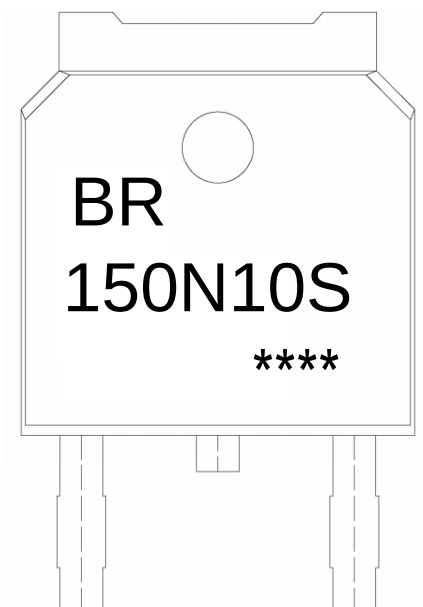


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DATA SHEET

/ Marking Instructions



BR

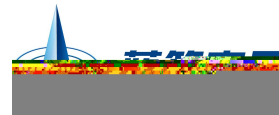
150N10S

Note:

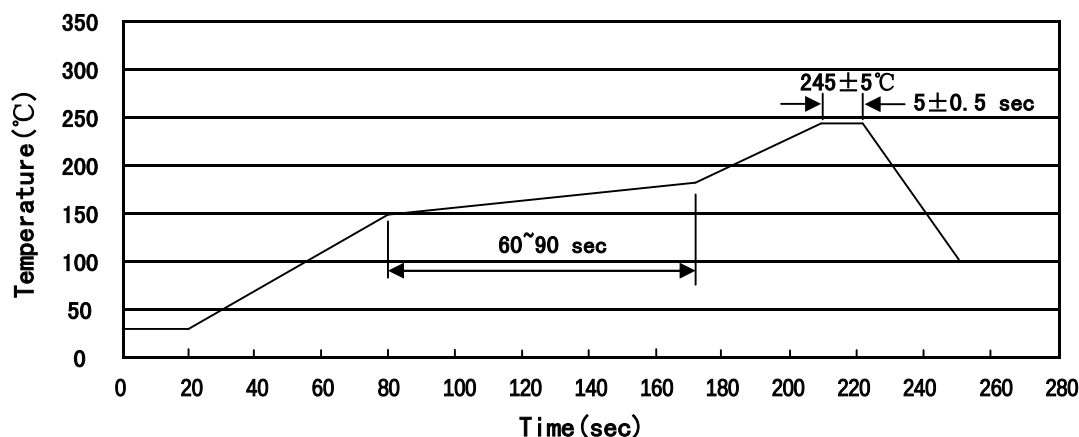
BR: Company Code

150N10S: Product Type Code

****: Lot No. Code, code change with Lot No



() / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-------|-----|----|-----------|--|
| 1 | 150 | 180 | 60 | 90sec; | 1.Preheating:150~180°C, Time:60~90sec. |
| 2 | 245±5 | | | 5±0.5sec; | 2.Peak Temp.:245±5°C, Duration:5±0.5sec. |
| 3 | | | 2 | 10°C/sec. | 3. Cooling Speed: 2~10°C/sec. |

/ Resistance to Soldering Heat Test Conditions

260±5°C 10±1 sec. Temp.:260±5°C Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
TO-252	2,500	2	5,000	6	30,000	13" ×16	360×360×50	380×335×366

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-251/252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180

/ Notices